

Device Modeling Report

COMPONENTS:

DIODE/ GENERAL PURPOSE RECTIFIER / PROFESSIONAL

PART NUMBER: 20GL2C41A

MANUFACTURER: TOSHIBA

REMARK: TC= 150C

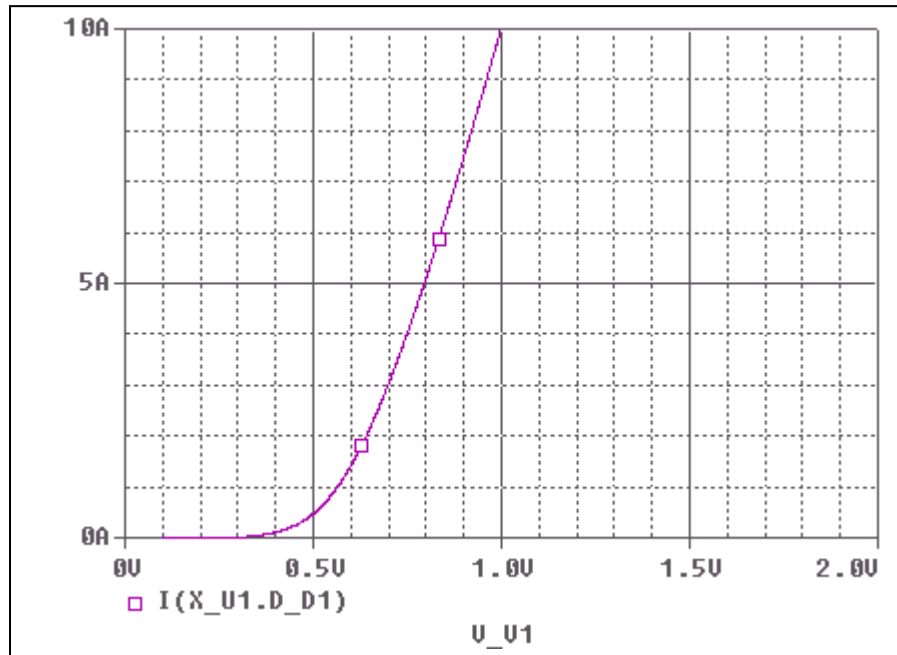


Bee Technologies Inc.

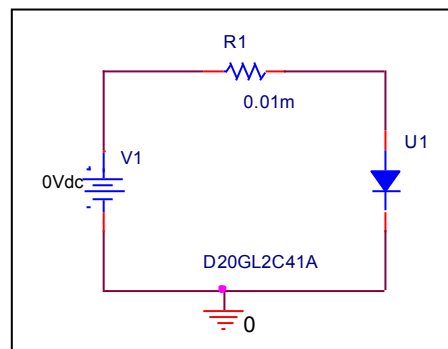
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristic

Circuit Simulation Result

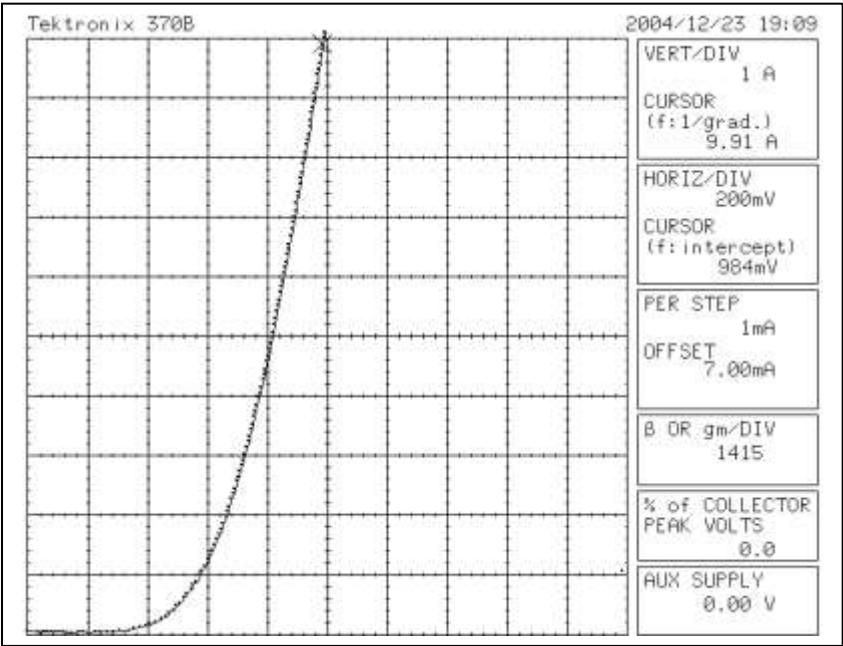


Evaluation Circuit



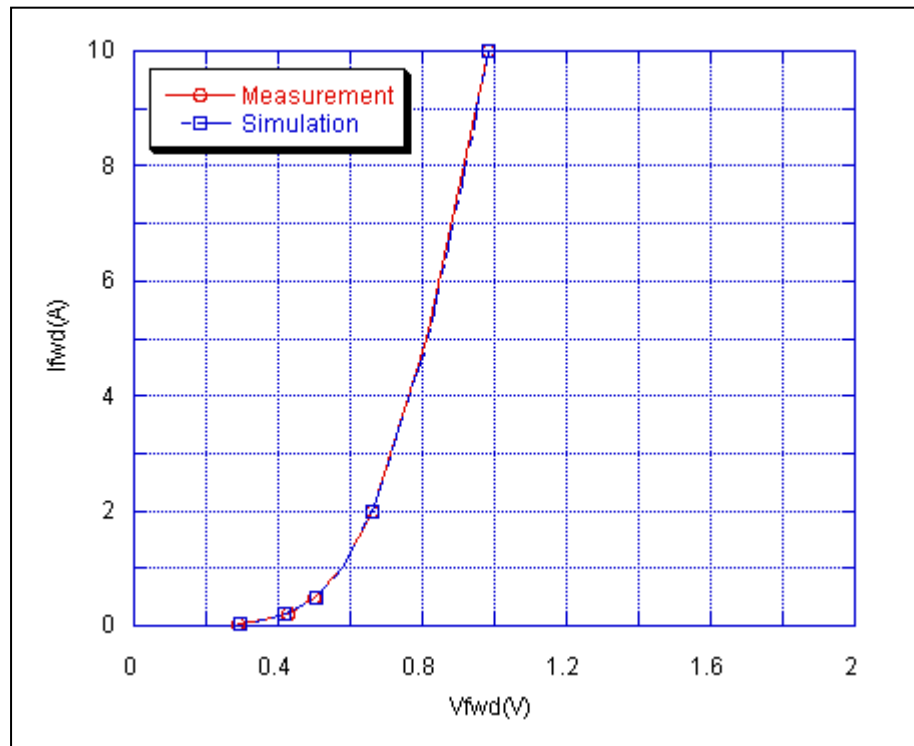
Forward Current Characteristic

Reference



Comparison Graph

Circuit Simulation Result

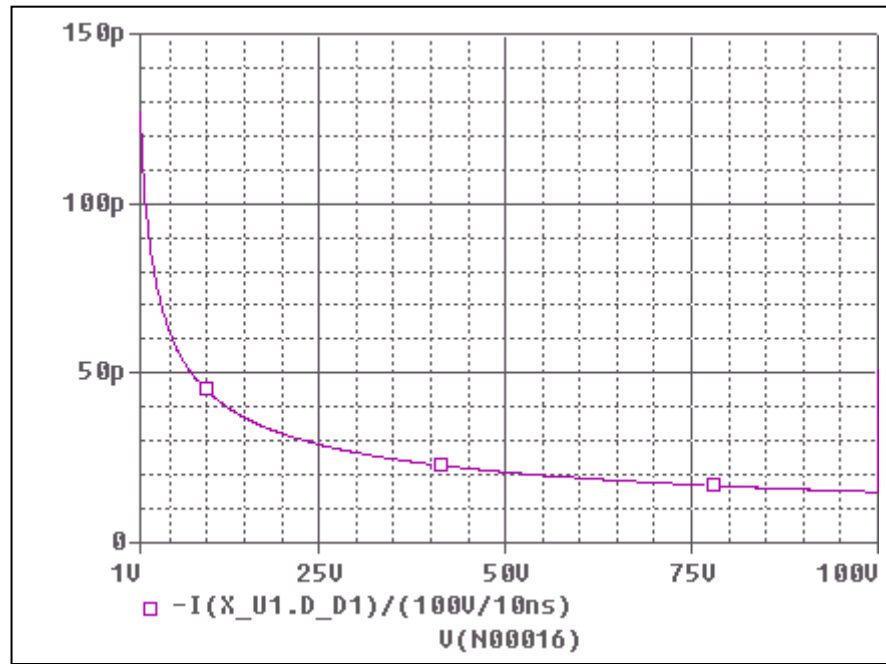


Simulation Result

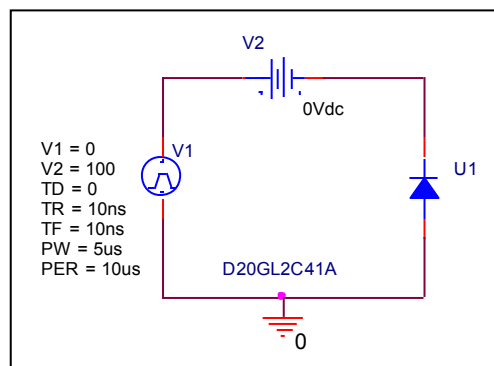
Ifwd(A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.05	0.290	0.295	-1.724
0.1	0.358	0.356	0.559
0.2	0.428	0.418	2.290
0.5	0.498	0.505	-1.406
1	0.578	0.578	-0.052
2	0.664	0.663	0.151
5	0.814	0.814	-0.025
10	0.984	0.984	-0.010

Capacitance Characteristic

Circuit Simulation Result

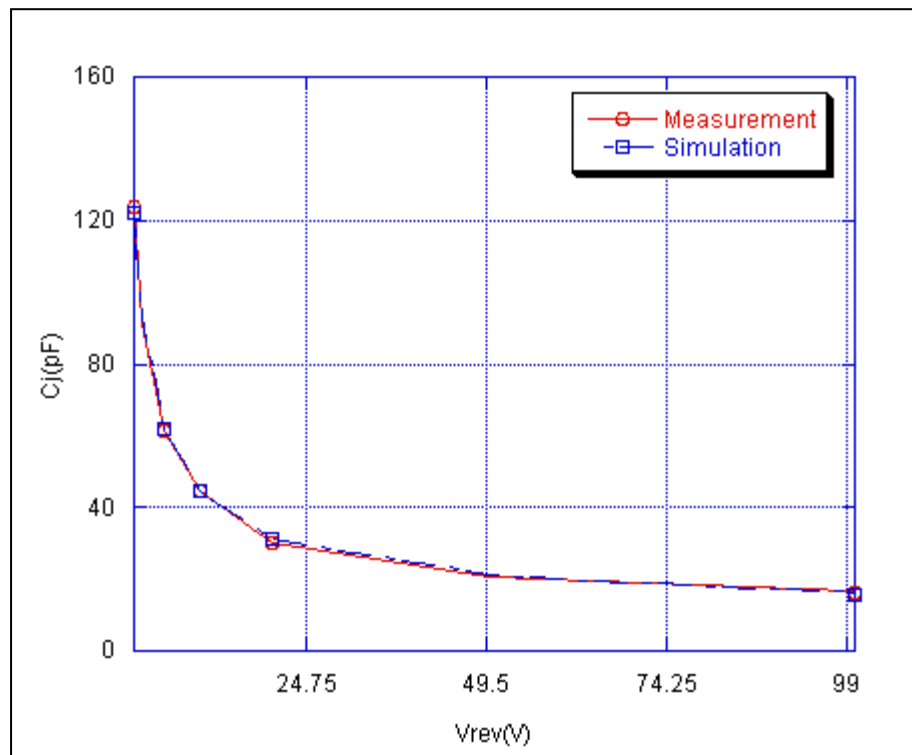


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

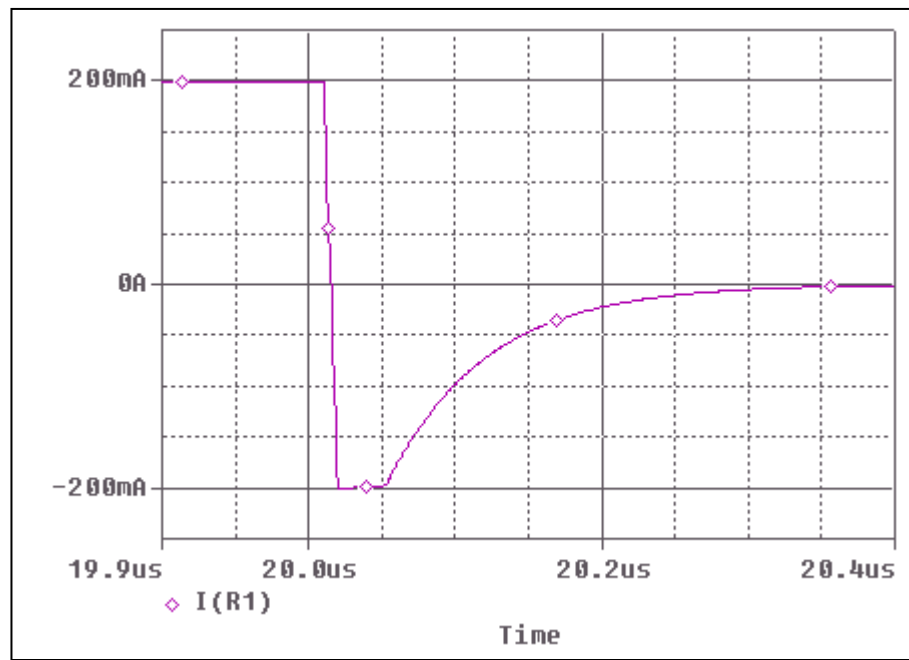


Simulation Result

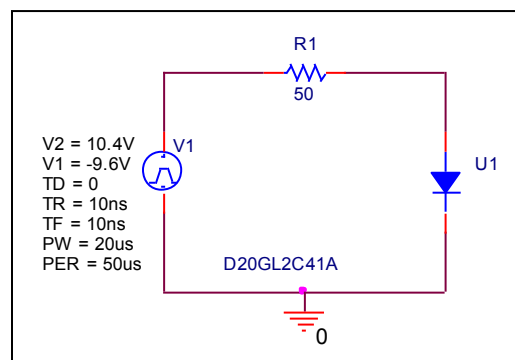
Vrev(V)	Cj(pF) Measurement	Cj(pF) Simulation	%Error
0	265.480	265.480	0.000
1	123.760	122.036	1.393
2	91.730	93.230	-1.635
5	61.220	61.890	-1.094
10	44.500	44.870	-0.831
20	30.050	31.350	-4.326
50	20.390	20.970	-2.845
100	16.300	15.570	4.479

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

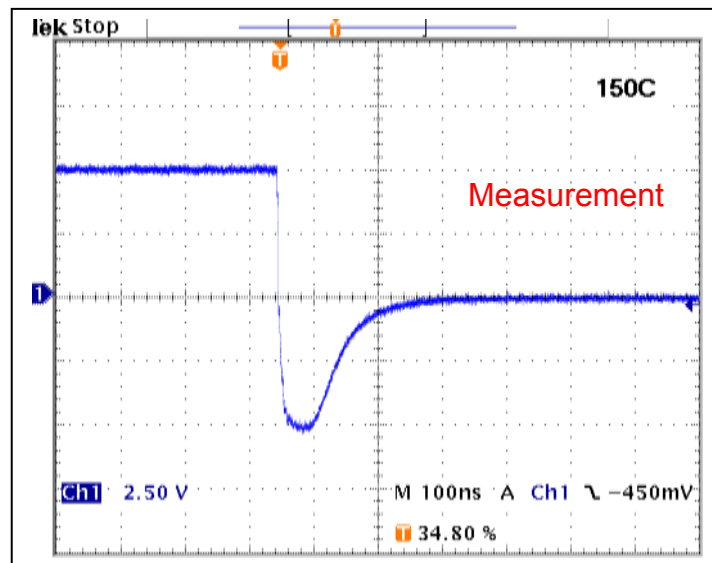


Compare Measurement vs. Simulation

	Measurement		Simulation		%Error
trj	38.00	ns	37.93	ns	0.184
trb	154.00	ns	153.97	ns	0.019

Reverse Recovery Characteristic

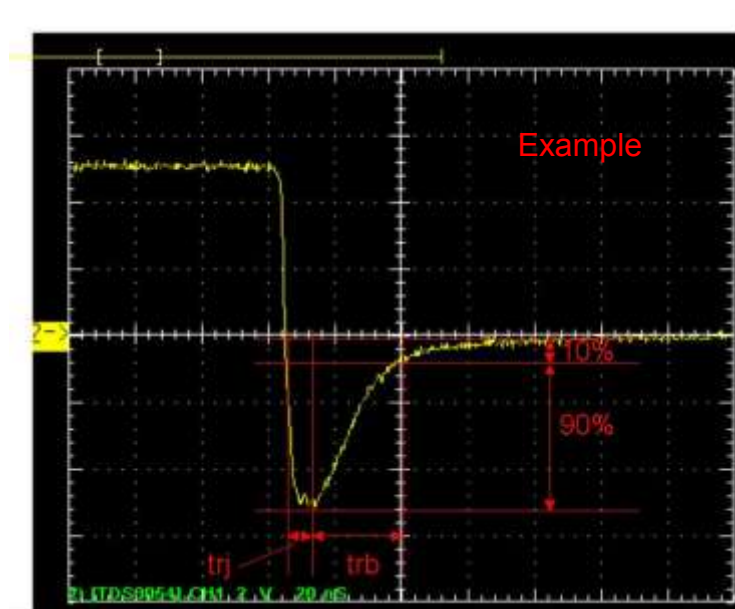
Reference



$T_{rj} = 38(\text{ns})$

$T_{rb} = 154(\text{ns})$

Conditions: $I_{fwd} = I_{rev} = 0.02(\text{A})$, $R_I = 50$



Relation between t_{rj} and t_{rb}